IN THE CLAIMS

Claims 1 - 16 (Cancelled)

17. (Previously Presented) An integrated circuit (IC) comprising:

a substrate;

an oxide layer formed directly on a surface of the substrate;

an adhesion layer formed on a surface of said oxide layer by treating said surface of said oxide layer with a gas; and

a first passivation layer formed on said adhesion layer, said first passivation layer and said adhesion layer including at least one common chemical element.

18. (Original) The integrated circuit of claim 17 further comprising a second passivation layer formed upon said first passivation layer.

19. (Previously Presented) The integrated circuit of claim 17 wherein said oxide layer includes silicon dioxide (SiO_2).

20. (Original) The integrated circuit of claim 17 wherein said adhesion layer includes silicon oxynitride.

21. (Original) The integrated circuit of claim 17 wherein said first passivation layer includes silicon nitride (Si_3N_4).

22. (Original) The integrated circuit of claim 18 wherein said second passivation layer includes polyimide.

23. (Previously Presented) An integrated circuit comprising in a three layer stack:

a silicon dioxide insulating layer;

a silicon oxynitride adhesion layer formed on a surface of said silicon dioxide insulating layer by treating said surface of said silicon dioxide insulating layer with a gas; and

a silicon nitride hard passivation layer formed directly on a surface of said silicon oxynitride adhesion layer.

24. (Original) The integrated circuit passivation layer of claim 23 further comprising a photodefinable polyimide soft passivation layer formed on said silicon nitride hard passivation layer.

25. (Previously Presented) The integrated circuit of claim 17, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH_3), oxygen and argon (Ar) and ozone (O_3) and argon.

26. (Previously Presented) The integrated circuit of claim 23, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH_3), oxygen and argon (Ar) and ozone (O_3) and argon.

27. (Currently Amended) An integrated circuit comprising:

a substrate;

a composite film formed on the substrate, the composite film comprising:

a first layer comprising silicon dioxide,

a second layer formed from a modification of a portion of the first layer, and

a third layer of a material different than a material of the second layer,

~~wherein each of the first layer, the second layer, and the third layer are distinguishable,~~

wherein the second layer is disposed between the first layer and the third layer, and

wherein the second layer and the third layer comprise one common chemical element other than silicon; and

wherein the third layer is a passivation layer formed on the second layer.

28. (Previously Presented) The integrated circuit of claim 27 wherein said second layer includes silicon oxynitride.

29. (Previously Presented) The integrated circuit of claim 27 wherein said third layer includes silicon nitride (Si3N4).